Level shifter circuit

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Abstract

A level shifter circuit of the preferred embodiment can be used as a transfer gate driver of a memory circuit such as a DRAM. A pair of cross-coupled transistors receives a first potential. A plurality of transistors are coupled between the pair of cross-coupled transistors and a second potential. An output unit has a pull-down switch for providing an output signal of one of first, second and third potentials and are coupled to the pair of cross-coupled transistor and the plurality of transistors. The third potential has a potential between the first and second potentials

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(54) **LEVEL SHIFTER CIRCUIT**

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(58) **Field of Search** 326/81, 80, 82, 326/83, 68, 59, 60; 365/189.11

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(57) **ABSTRACT**

A level shifter circuit of the preferred embodiment can be used as a transfer gate driver of a memory circuit such as a DRAM. A pair of cross-coupled transistors receives a first potential. A plurality of transistors are coupled between the pair of cross-coupled transistors and a second potential. An output unit has a pull-down switch for providing an output signal of one of first, second and third potentials and are coupled to the pair of cross-coupled transistor and the plurality of transistors. The third potential has a potential between the first and second potentials.

13 Claims, 5 Drawing Sheets